

MA860

Silicon epitaxial planer type

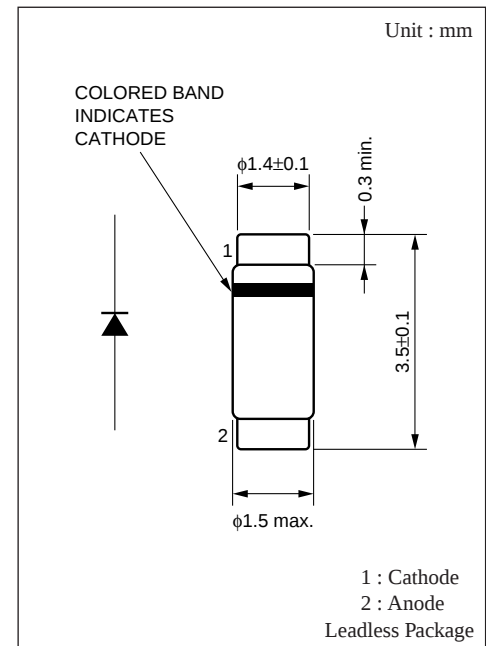
For band switching

■ Features

- Extra-small cylindrical package, optimum for high-density mounting
- Less voltage dependence of the capacity C_t between pins
- Low forward dynamic resistance r_f
- Optimum for a band switching of tuner

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}	– 25 to + 85	°C
Storage temperature	T_{stg}	– 55 to +100	°C



■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R * 1	$V_R = 33V$			100	nA
Forward voltage (DC)	V_F	$I_F = 100mA$			1.0	V
Terminal capacitance	C_t	$V_R = 6V, f = 1MHz$		0.8	1.2	pF
Forward dynamic resistance	r_f * 2	$I_F = 2mA, f = 100MHz$		0.5	0.65	Ω
	r_f * 3			0.77	0.98	Ω

Note 1 : Rated input/output frequency : 100MHz

2 : * 1 Measurement with the beam shielded

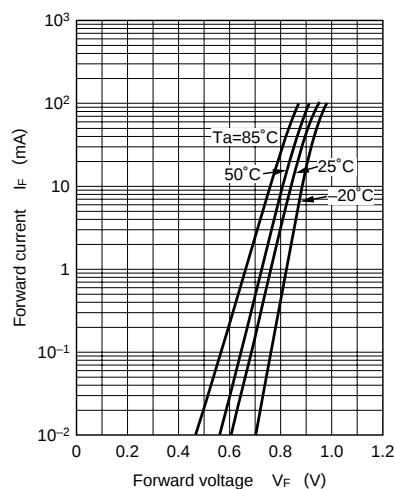
* 2 r_f measurement device : Nihon Koshuha MODEL TDC-121 A

* 3 r_f measurement device : YHP 4191A RF IMPEDANCE ANALYZER

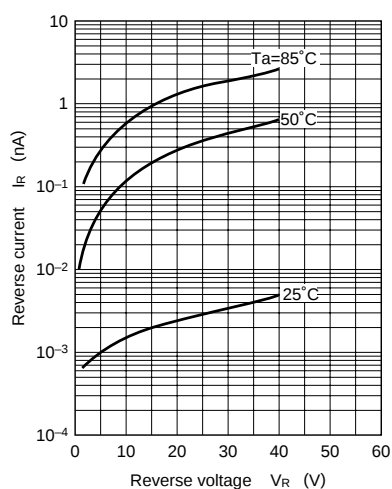
■ Cathode Indication

Type No.	MA860
Color	Blue

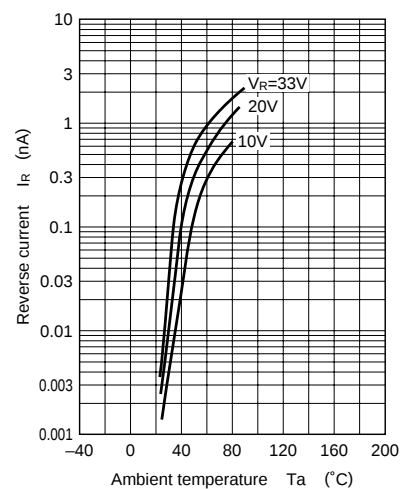
$I_F - V_F$



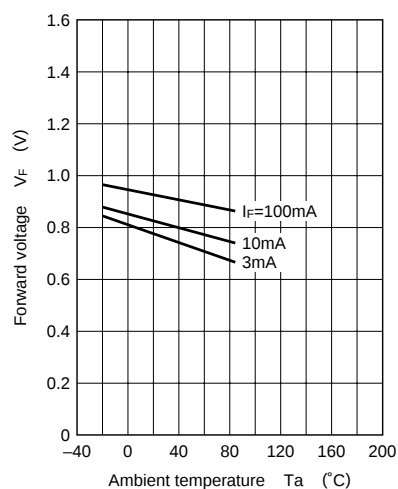
$I_R - V_R$



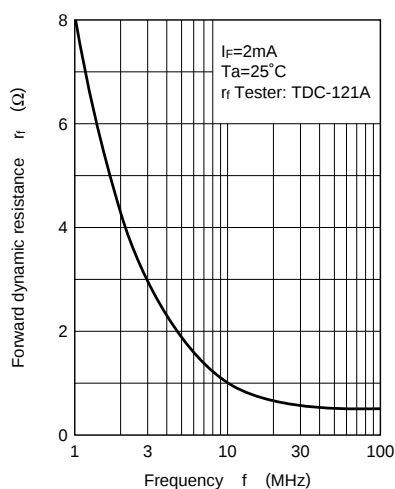
$I_R - T_a$



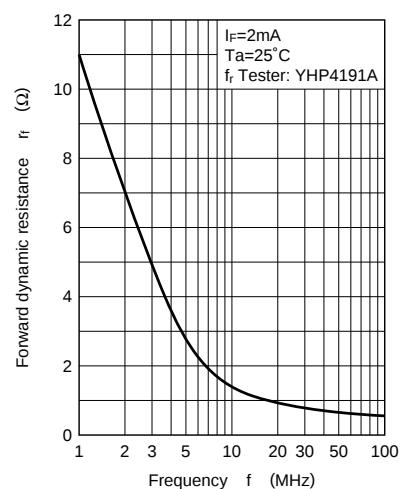
$V_F - T_a$



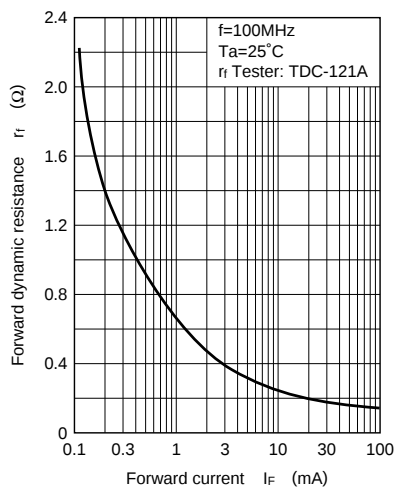
$r_f - f$



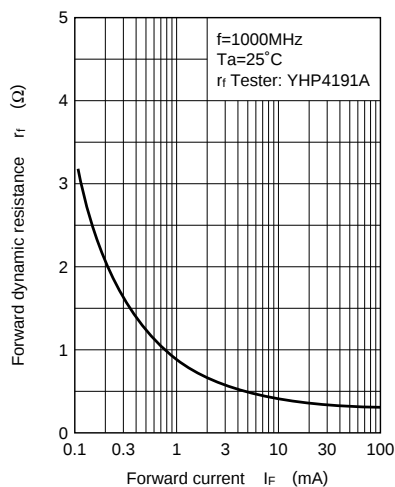
$r_f - f$



$r_f - I_F$



$r_f - I_F$



$C_D - V_R$

